



INDIAN INSTITUTE OF TECHNOLOGY KHARAGPUR
Mid-Autumn Semester 2019-20

Date of Examination: 20-09-2019 Session: AN Duration 2 hrs Full Marks: 60
Subject No. : EC21103 Subject: Introduction to Electronics
Department/Center/School:
Department of Electronics and Electrical Communication Engineering
Specific charts, graph paper, log book etc., required: No

• **Instructions**

- Answer all questions (Question no. 1 to 6). Answers must be brief and to the point.
- Avoid writing answers of the various parts of a single question at different locations in your answer-script. For every Question No., start your answer from a new page.
- The final answers (numerical values with unit) should be underlined or enclosed within box with unit.
- Show the necessary steps in your answers with high clarity and supported explanation.
- All waveform sketches / diagrams must be neatly drawn and clearly labeled.
- For any value related to any device parameter or circuit parameter, which you may find not given with a problem, assume suitable value for such parameter and write your assumptions.

Note: Assume, V_Y (cut-in voltage for Silicon diodes) = 0.7 V and $V_{BE(ON)} = 0.7$ V for n-p-n BJT unless otherwise mentioned.

1. Multiple choice questions (Only one correct answer) 10x1=10

- I. The peak inverse voltage of the Silicon diode in a half-wave rectifier circuit with capacitor filter is
 - (a) V_m
 - (b) $2 V_m$
 - (c) $V_m - V_Y$
 - (d) $2V_m - V_Y$Where V_m is the maximum amplitude of input sinusoid signal.
- II. Proper DC biasing is required in a CE amplifier to
 - (a) set the transistor gain
 - (b) set the transistor in active regime
 - (c) both (a) and (b)
 - (d) none of (a) and (b)
- III. Forward-bias voltage across a silicon p-n junction diode is increased by 60 mV, the diode current is expected to increase by
 - (a) 2 times
 - (b) 4 times
 - (c) 6 times
 - (d) 10 times
- IV. Reverse saturation current of a p-n junction diode becomes double with
 - (a) every 10 °C fall in temperature
 - (b) every 10 °C rise in temperature
 - (c) every 2 °C fall in temperature
 - (d) every 100 °C rise in temperature

- V. In a p-type silicon sample the hole concentration is $2.25 \times 10^{15}/\text{cm}^3$. The intrinsic carrier concentration is $1.5 \times 10^{10}/\text{cm}^3$, the electron concentration is
 (a) $1.5 \times 10^{10} \text{ cm}^{-3}$ (b) $2.25 \times 10^{15} \text{ cm}^{-3}$
 (c) 10^5 cm^{-3} (d) Zero
- VI. The input to a half-wave rectifier without a filter is $v_i = 18.84 \sin 314.2t$. The dc component at the output will be
 (a) 4.25 V (b) 6 V (c) 9.42 V (d) 13.3 V
- VII. A 4 V DC voltage source is connected to a voltage regulator using a Zener diode with $V_z = 6 \text{ V}$. The load voltage is
 (a) 0 (b) 4 V
 (c) 6 V (d) depends on the load resistance value
- VIII. Magnitude of ripple factor for a simple half-wave rectifier (without any filter circuit) is
 (a) 1.21 (b) 0.48
 (c) 0.81 (d) 0.99
- IX. In a silicon npn BJT, the base to emitter voltage (V_{BE}) is 0.7 V and collector to base voltage (V_{CB}) is 0.2 V. The transistor is operating in the
 (a) Cut – off mode (b) Saturation mode
 (c) Forward active mode (d) Inverse active mode
- X. In a bipolar junction transistor Early – effect is caused by
 (a) Fast turn – off. (b) Fast turn – on.
 (c) Large collector–base reverse bias. (d) Large emitter–base forward bias
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2.(a) (i) Why does Semiconductors display/exhibit an electronic bandgap? Explain with suitable diagrams. (ii) How can you modulate the conductivity of a semiconductor? **[3+2]**

Note: Remember, NO marks will be given if you write WHAT a Bandgap is? We are asking WHY Bandgap exists?

2.(b) What are the fundamental differences between the working principles of a Diode and a Bipolar Junction Transistor (BJT)? Give at least **five** differences. **[5]**

3.(a) (i) With suitable circuits, diagrams and plots/graphs explain the Input and Output characteristics of a **PNP** bipolar junction transistor in common emitter (**CE**) configuration. (ii) How does Early effect influences the gain of a CE amplifier? **[6+2]**

3.(b) Assuming ideal Diodes, determine I_D , V_{D2} and V_o for the circuit in shown in Figure 1 (next page). **[2]**

4. For the Circuit shown in Figure 2 the following information are available. The transformer has a turns ratio of 8:1 and the input rms voltage varies from 110 V to 120 V at 60 Hz. All diodes in the bridge rectifier are made up of silicon. The Zener voltage is fixed at 12 V and the Zener resistance is $2\ \Omega$. The Zener diode could operate over the range of 10 mA to 100 mA.

It is expected that output load current (I_L) should vary between 25 mA and 50 mA and the output voltage (V_o) remains within 12 to 12.20 V.

Determine the appropriate values of the Resistors (R_i and R_L) and Capacitor (C) that will allow you to produce such output voltage and currents. **(10)**

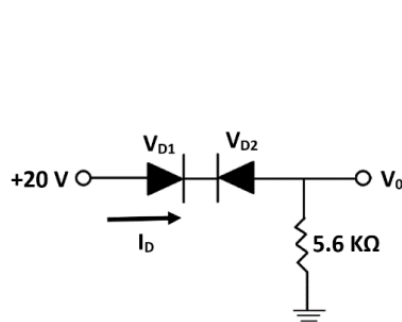


Figure 1

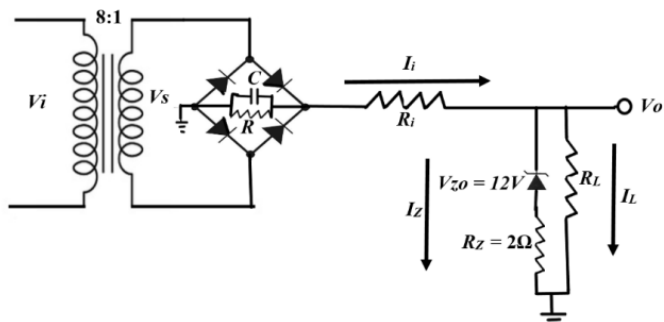


Figure 2

5.(a) (i) In the circuit shown in Figure 3 if the voltage source (V_{in}) provides a sinusoidal signal of 12 V_{p-p} (+6 0 -6 V), estimate the maximum output voltage (V_{out}). (ii) Plot the output (V_{out}) waveform for at least $2T$, where, T is the time period of the input signal.

For this question assume $V_Y = 0$.

(2+3)

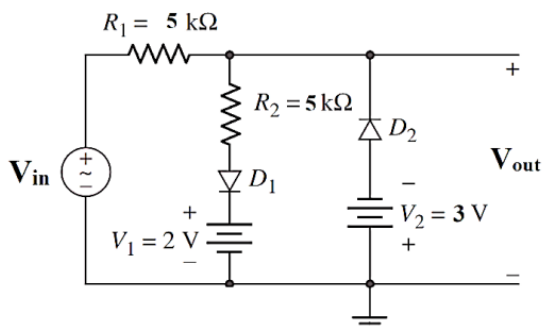


Figure 3

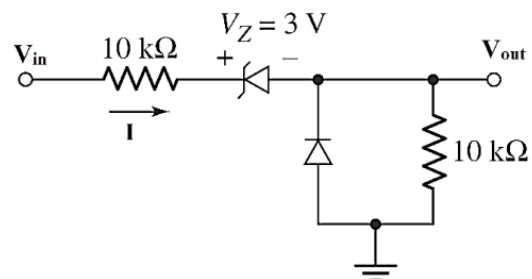


Figure 4

5.(b) In the circuit shown in Figure 4, the Zener breakdown voltage is 3 V. Plot the V_{out} vs V_{in} and I vs V_{in} if the input voltage (V_{in}) is varied from -10 V to +10 V. For this question assume $V_Y = 0$. **(2.5+2.5)**

6.(a) (i) In the circuit shown in Figure 5 determine the range of V_1 such that $2\text{ V} \leq V_{CE} \leq 4\text{ V}$. **(ii)** Sketch the load line with clear leveling and show the range of the Q-point values. Given that $\beta = 25$. **(3+1)**

6.(b) In the CE amplifier circuit shown in Figure 6 assume $V_{CC} = 15\text{ V}$, $\beta = 150$, $V_{BE} = 0.7\text{ V}$, $R_E = 1\text{ k}\Omega$, $R_C = 4.7\text{ k}\Omega$, $R_1 = 47\text{ k}\Omega$, $R_2 = 10\text{ k}\Omega$, $R_L = 47\text{ k}\Omega$, $R_s = 100\text{ }\Omega$.

(i) Determine the Q-point. **(ii)** Draw the AC equivalent circuit and determine the AC model parameters. **(iii)** Estimate small-signal voltage gain. **(2+2+2)**

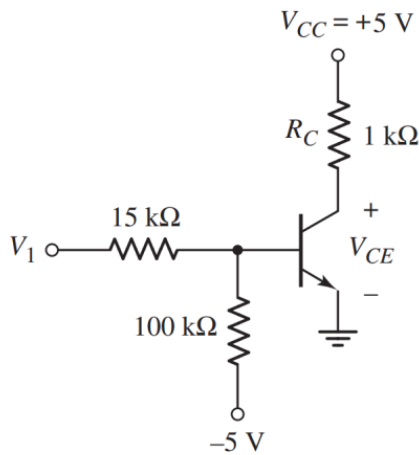


Figure 5

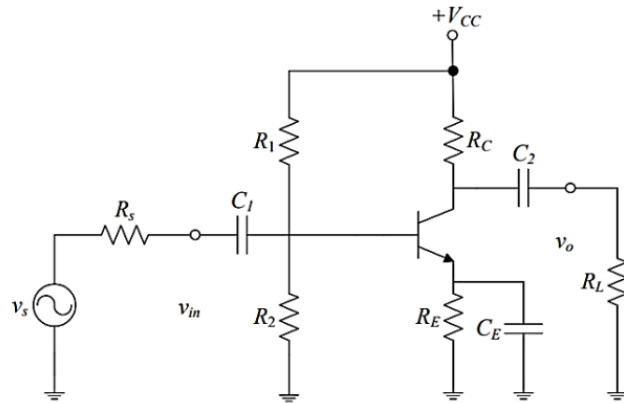


Figure 6

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